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(54) **POWER AMPLIFICATION MODULE**

(58) **Field of Classification Search**

None

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See application file for complete search history.

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(73) Assignee: **MURATA MANUFACTURING CO., LTD.**, Kyoto (JP)

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

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(51) **Int. Cl.**

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H03G 3/30	(2006.01)
H03F 3/191	(2006.01)
H03F 3/21	(2006.01)
H03F 3/24	(2006.01)

(57) **ABSTRACT**

Provided is a power amplification module that includes: a first transistor, a first signal being inputted to a base thereof; a second transistor, the first signal being inputted to a base thereof and a collector thereof being connected to a collector of the first transistor; a first resistor, a first bias current being supplied to one end thereof and another end thereof being connected to the base of the first transistor; a second resistor, one end thereof being connected to the one end of the first resistor and another end thereof being connected to the base of the second transistor; and a third resistor, a second bias current being supplied to one end thereof and another end thereof being connected to the base of the second transistor.

(52) **U.S. Cl.**

CPC **H03G 3/3042** (2013.01); **H03F 3/191** (2013.01); **H03F 3/211** (2013.01); **H03F 3/245** (2013.01); **H03F 2200/18** (2013.01); **H03F 2200/324** (2013.01); **H03F 2200/451** (2013.01); **H03F 2203/21181** (2013.01)

6 Claims, 6 Drawing Sheets

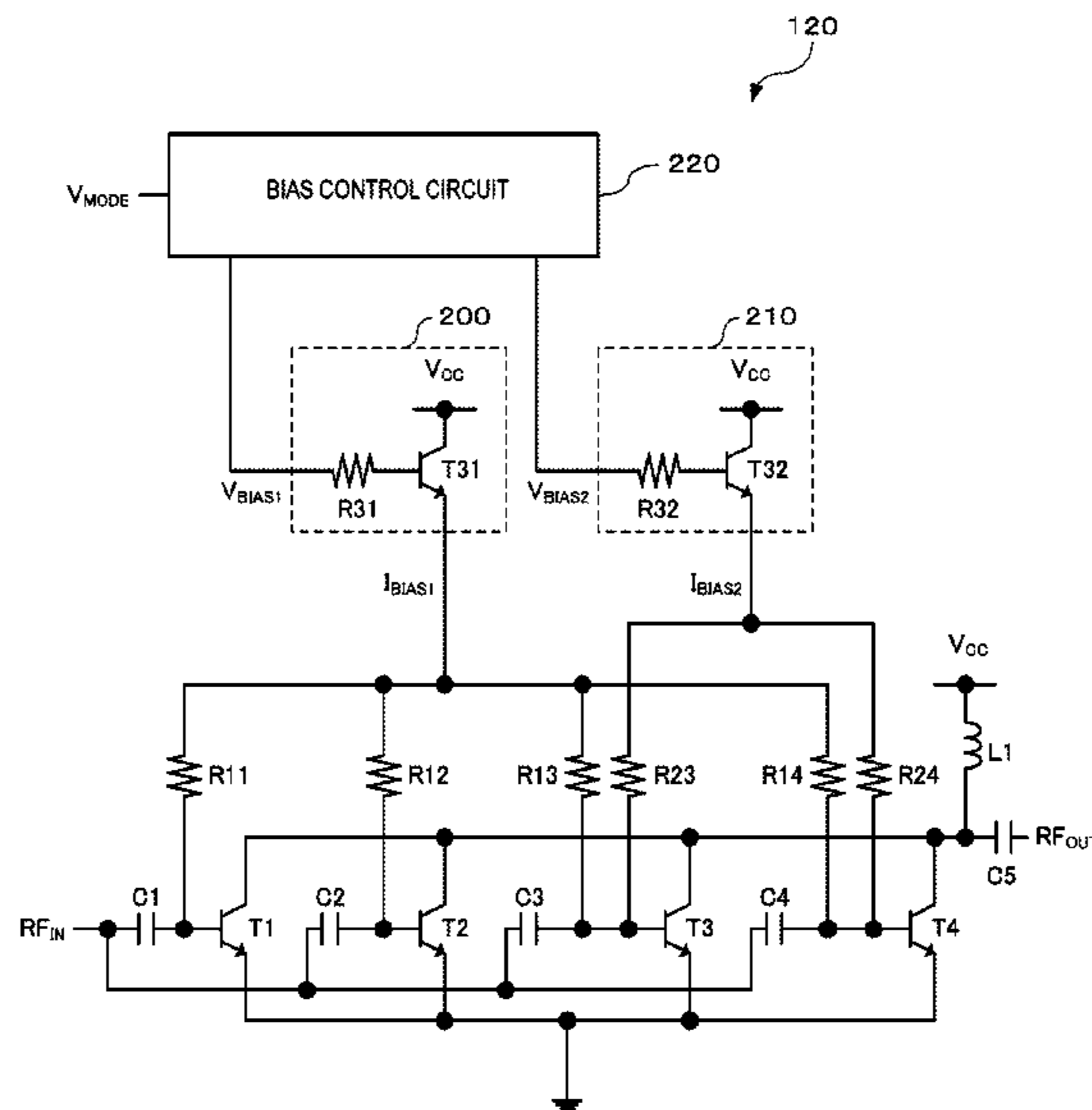


FIG. 1

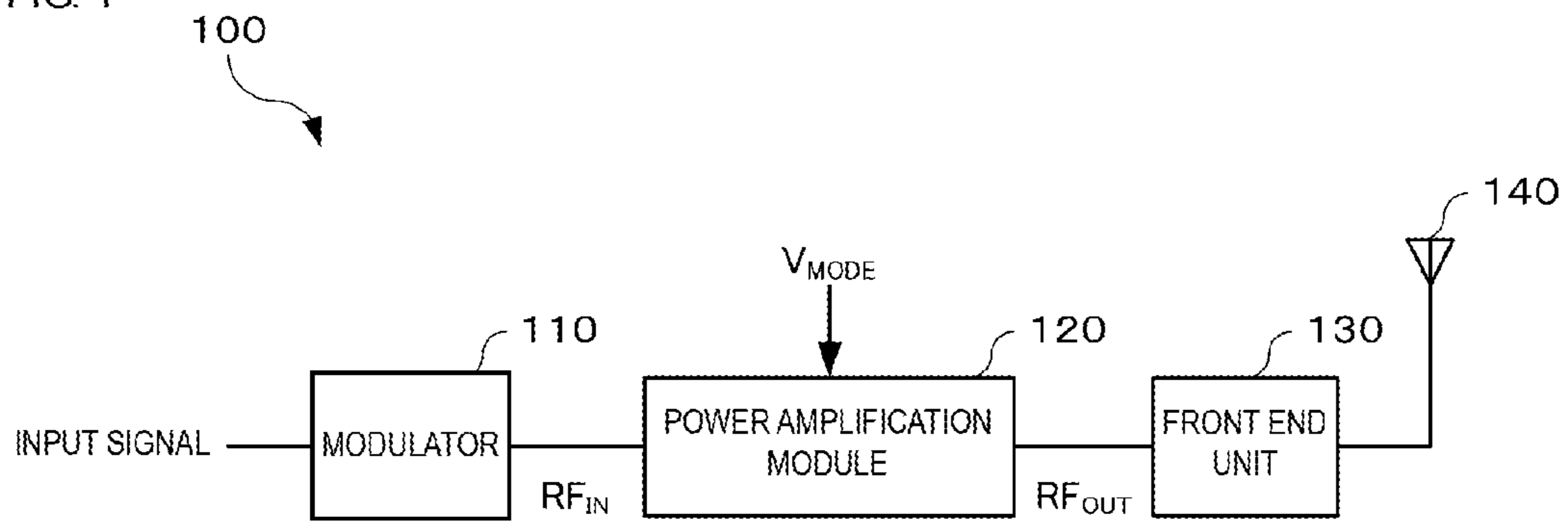


FIG. 2

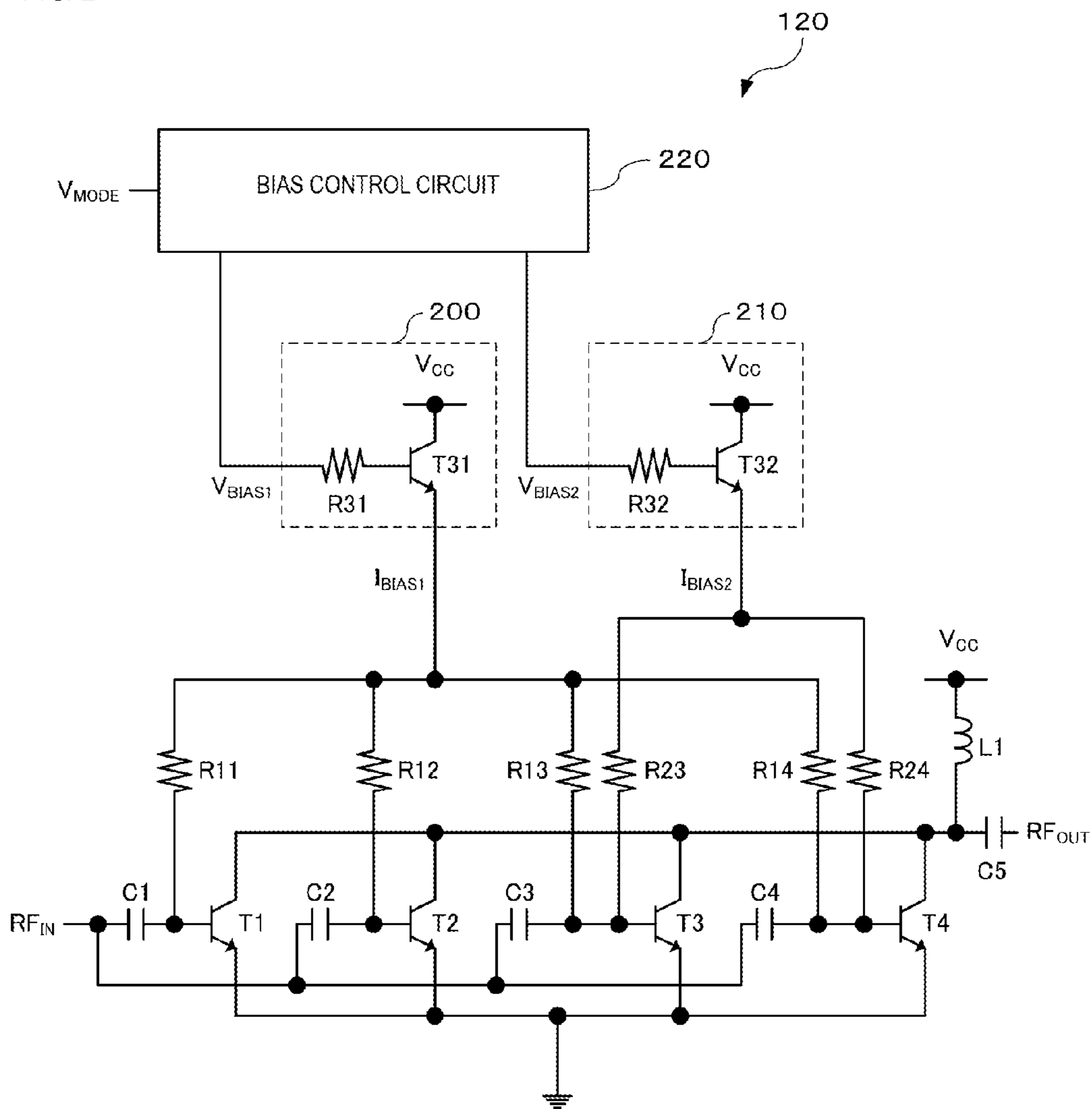


FIG. 3

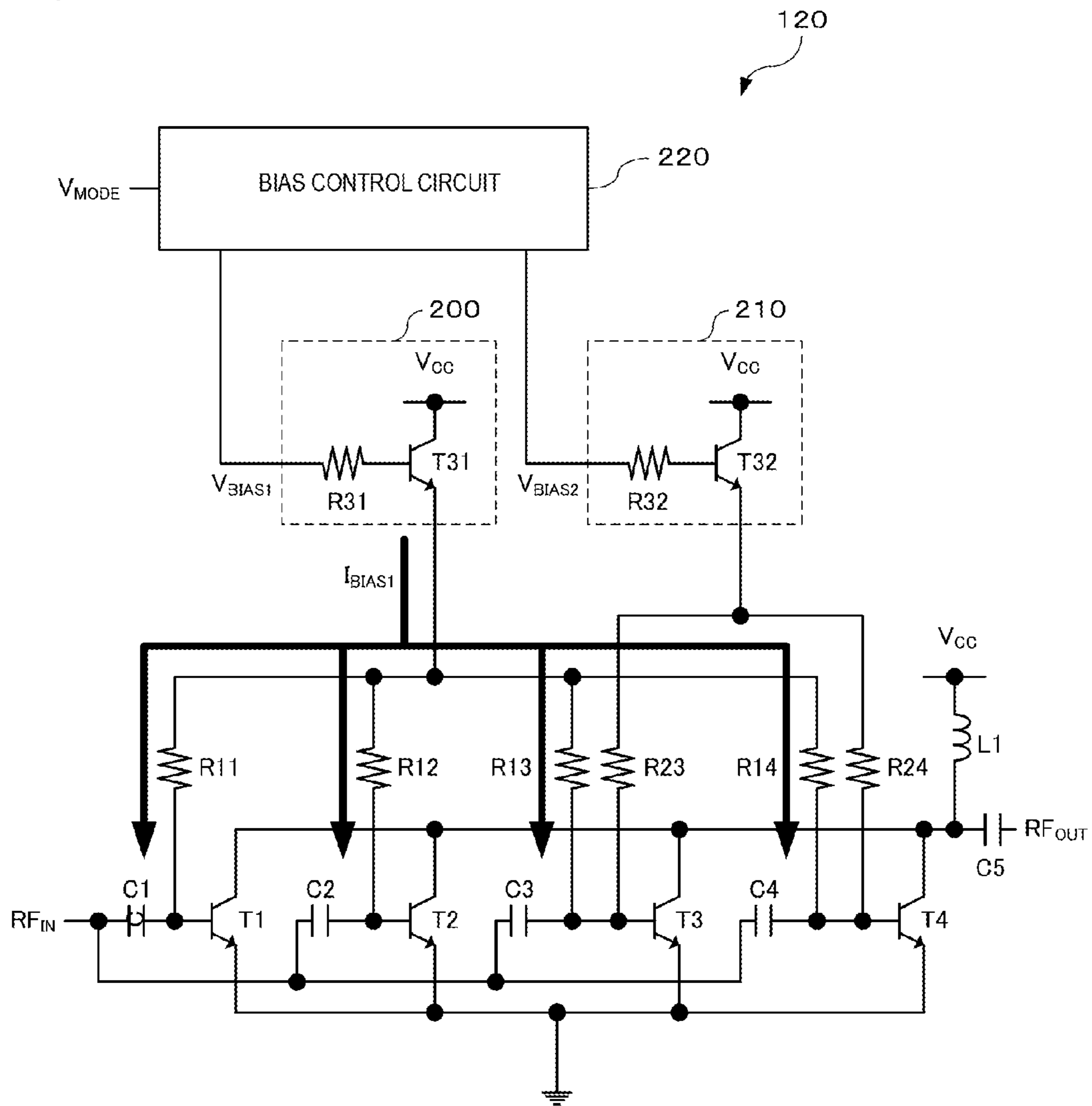


FIG. 4

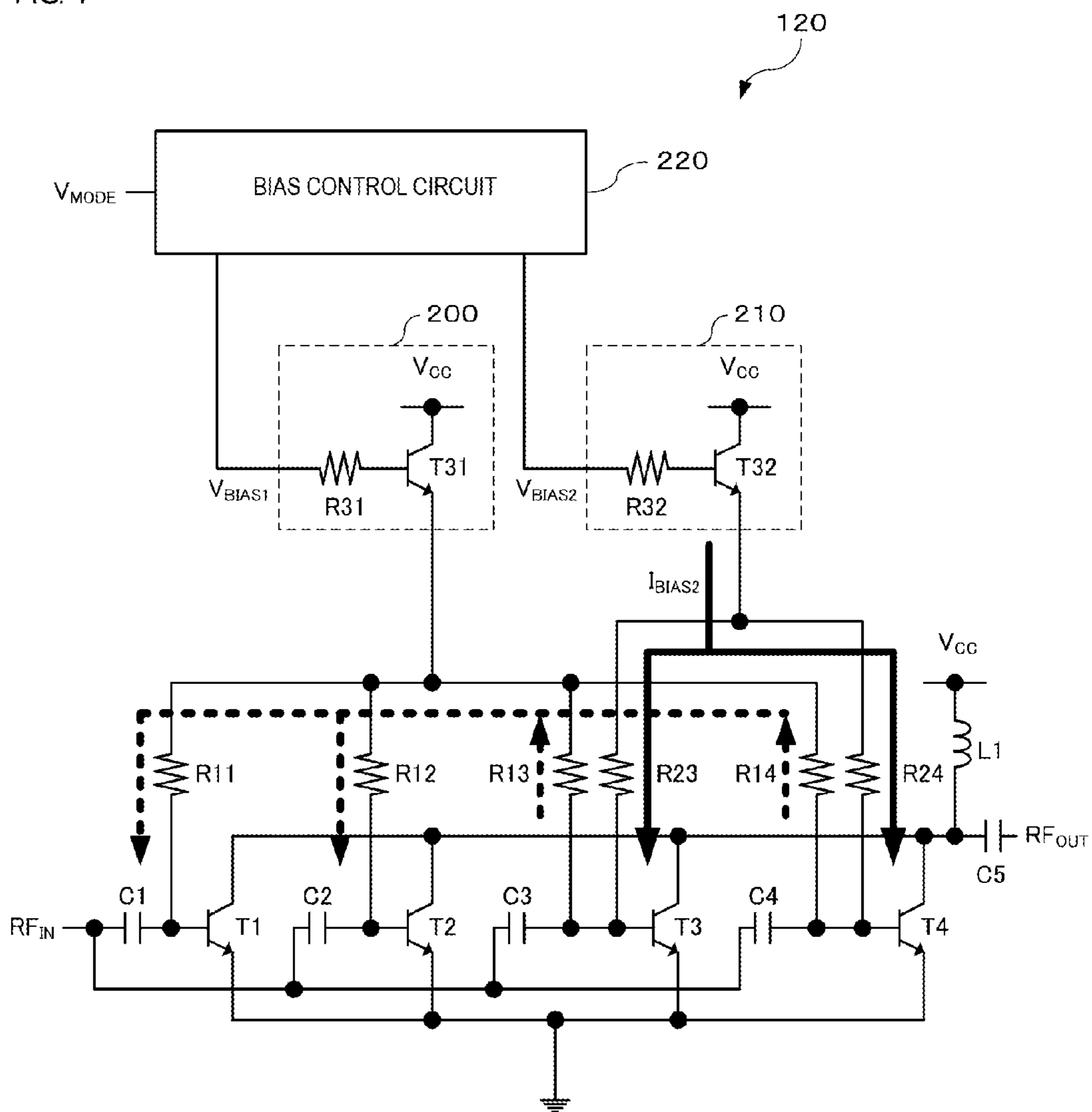


FIG. 5

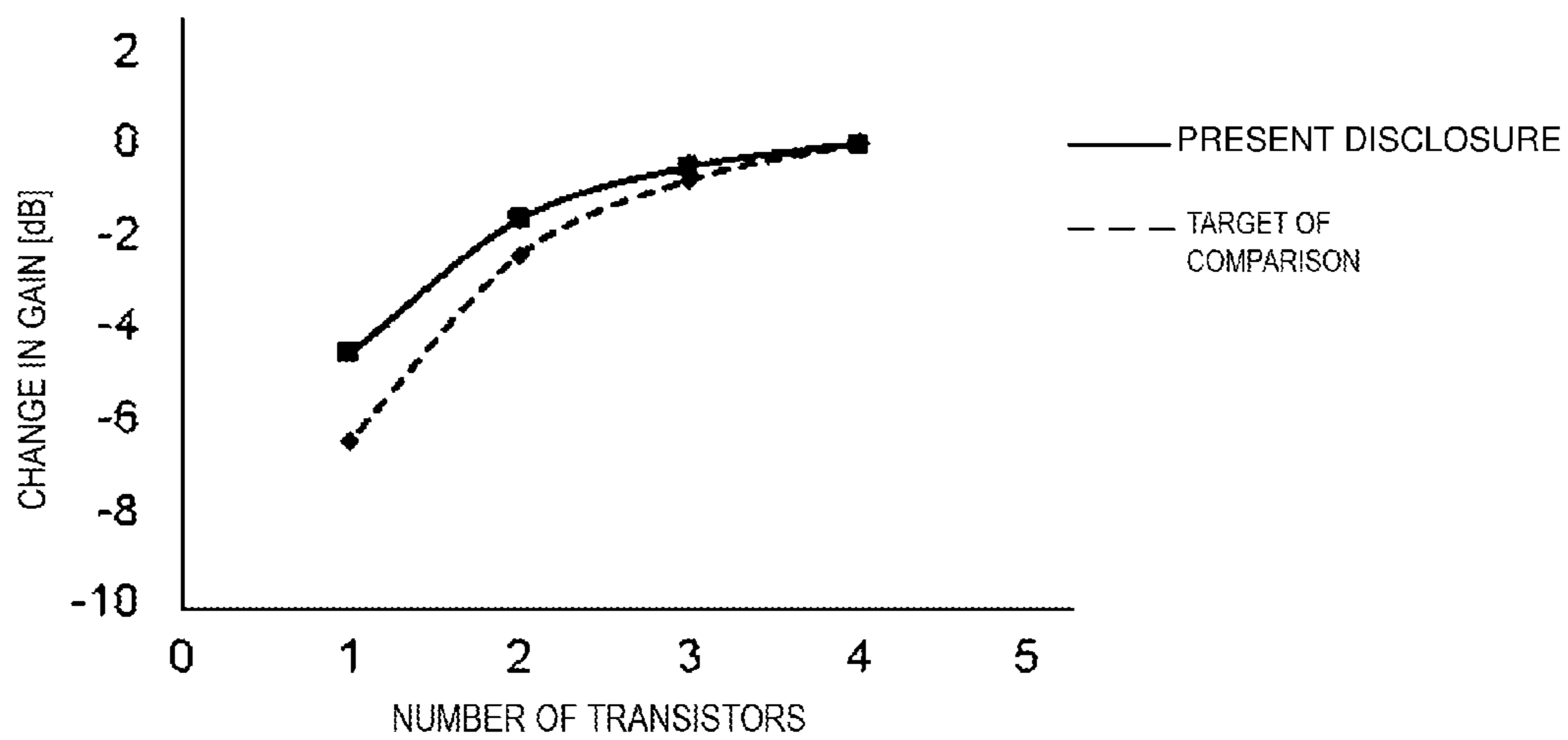
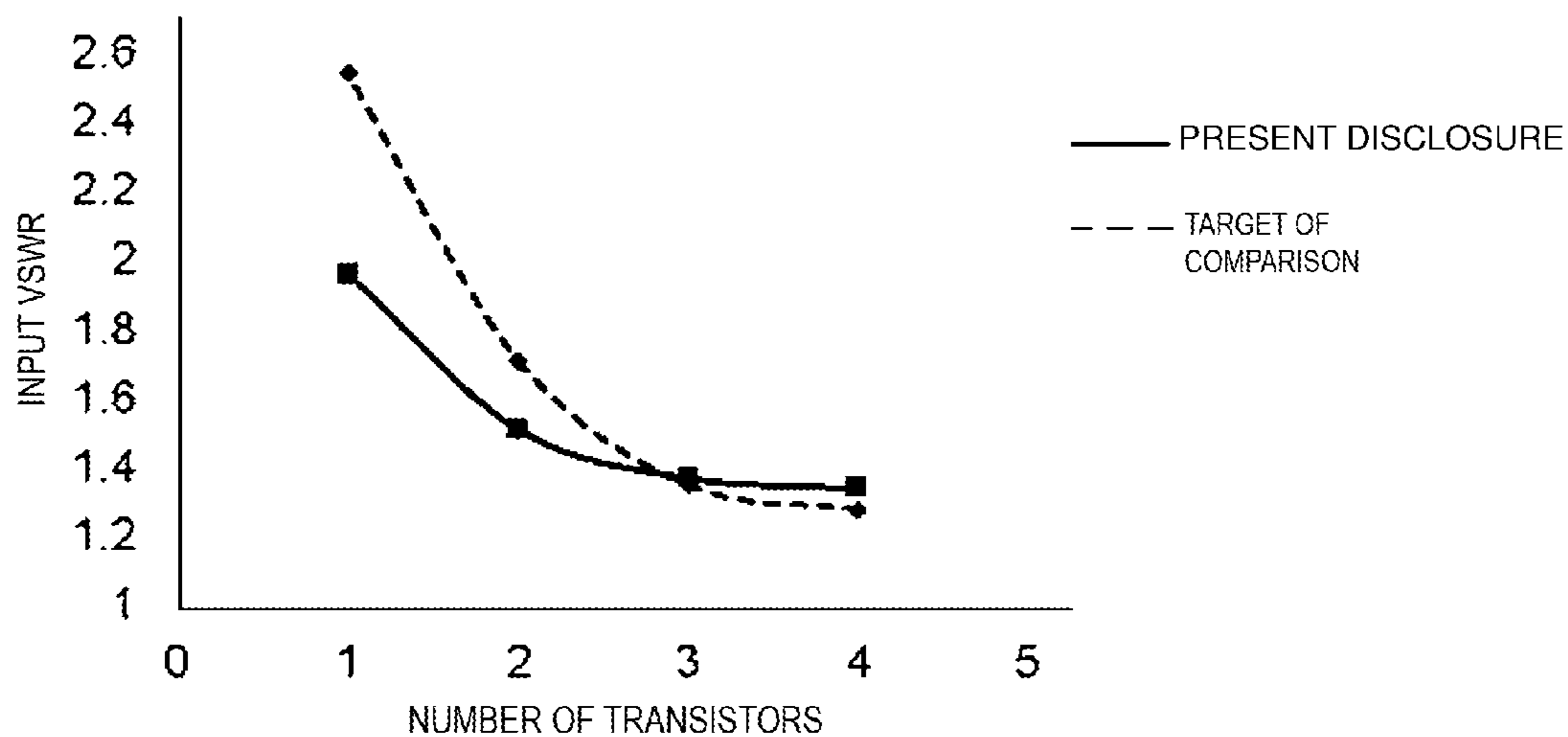


FIG. 6



POWER AMPLIFICATION MODULE

BACKGROUND OF THE DISCLOSURE

1. Field of the Disclosure

The present disclosure relates to a power amplification module.

2. Description of the Related Art

A power amplification module is used in a mobile communication device such as a cellular phone in order to amplify the power of a signal to be transmitted to a base station. In such a power amplification module, the gain may be switched in accordance with the output level in order to improve the power addition efficiency. For example, in Japanese Unexamined Patent Application Publication No. 2004-128704, a configuration is disclosed in which the gain is adjusted by changing the current that flows to an amplifier of a power amplification module in a power amplification circuit formed of transistors that are connected in parallel with each other. In this configuration, variations in the input impedance that occur with a change in current are suppressed by a complicated large-scale control circuit mounted on the bias circuit side of the power amplification module.

However, there is a demerit in mounting a complicated large-scale control circuit in a power amplification module in order to suppress the variations in input impedance in that the chip area becomes larger. On the other hand, when the number of operating transistors is changed in order to adjust the gain, the input impedance of the power amplification circuit changes. Consequently, the voltage standing wave ratio (VSWR) at the input of the power amplification circuit may be degraded.

BRIEF SUMMARY OF THE DISCLOSURE

The present disclosure was made in light of such circumstances and it is an object thereof to suppress a change in input impedance that occurs with a change in gain in a power amplification module that is capable of changing the gain thereof.

A power amplification module according to a preferred embodiment of the present disclosure includes: first transistor, a first signal being inputted to a base thereof; a second transistor, the first signal being inputted to a base thereof and a collector thereof being connected to a collector of the first transistor; a first resistor, a first bias current being supplied to one end thereof and another end thereof being connected to the base of the first transistor; a second resistor, one end thereof being connected to the one end of the first resistor and another end thereof being connected to the base of the second transistor; and a third resistor, a second bias current being supplied to one end thereof and another end thereof being connected to the base of the second transistor. At the time of a high gain mode, the first bias current is supplied to the bases of the first and second transistors via the first and second resistors, respectively. At the time of a low gain mode, the second bias current is supplied to the base of the second transistor via the third resistor and is supplied to the base of the first transistor via the third, second and first resistors, and a second signal, which is obtained by amplifying the first signal, is outputted from the collectors of the first and second transistors.

According to the preferred embodiment of the present disclosure, a change in input impedance that occurs with a change in gain can be suppressed in a power amplification module that is capable of changing the gain thereof.

Other features, elements, characteristics and advantages of the present disclosure will become more apparent from the following detailed description of preferred embodiments of the present disclosure with reference to the attached drawings.

BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWINGS

FIG. 1 illustrates an example configuration of a transmission unit that includes a power amplification module according to an embodiment of the present disclosure;

FIG. 2 illustrates an example of the configuration of a power amplification module;

FIG. 3 is a diagram for explaining the operation of the power amplification module in the case of a high gain mode;

FIG. 4 is a diagram for explaining the operation of the power amplification module in the case of a low gain mode;

FIG. 5 illustrates an example of the relationship between the number of transistors and a change in gain; and

FIG. 6 illustrates an example of the relationship between the number of transistors and the voltage standing wave ratio.

DETAILED DESCRIPTION OF THE DISCLOSURE

Hereafter, an embodiment of the present disclosure will be described while referring to the drawings. FIG. 1 illustrates an example configuration of a transmission unit that includes a power amplification module according to an embodiment of the present disclosure. A transmission unit **100** is for example used in a mobile communication device such as a cellular phone in order to transmit various signals such as speech and data to a base station. Although such a mobile communication device would also be equipped with a reception unit for receiving signals from the base station, the description of such a reception unit is omitted here.

As illustrated in FIG. 1, the transmission unit **100** includes a modulator **110**, a power amplification module **120**, a front end unit **130** and an antenna **140**.

The modulator **110** modulates an input signal on the basis of a modulation scheme such as high speed uplink packet access (HSUPA) or long term evolution (LTE) and generates a radio frequency (RF) signal for performing wireless transmission. The RF signal has a frequency of around several hundred MHz to several GHz, for example.

The power amplification module **120** amplifies the power of the RF signal (RF_{IN}) outputted from the modulator **110** up to the level that is required to transmit the RF signal to the base station, and outputs an amplified signal (RF_{OUT}). The power amplification module **120** operates in a gain mode that corresponds to a gain mode control voltage V_{MODE} . The gain mode may be a high gain mode or a low gain mode, for example.

The front end unit **130** filters the amplified signal and switches a reception signal received from the base station. The amplified signal outputted from the front end unit **130** is transmitted to the base station via the antenna **140**.

FIG. 2 illustrates an example of the configuration of the power amplification module **120**. The power amplification module **120** includes transistors T1, T2, T3 and T4, capacitors C1, C2, C3, C4 and C5, resistors R11, R12, R13, R14, R23 and R24, an inductor L1, bias circuits **200** and **210** and a bias control circuit **220**.

The transistors T1 to T4 are amplification transistors and are heterojunction bipolar transistors (HBTs), for example.

The transistors T1 to T4 are connected in parallel with one another and form a single amplification circuit. Each of the transistors T1 to T4 can serve as one finger of a multi-finger transistor. The RF signal (RF_{IN}) is inputted to the bases of the transistors T1 to T4 via the capacitors C1 to C4, respectively. In addition, a power supply voltage V_{CC} is supplied to the collectors of the transistors T1 to T4 via the inductor L1. The transistors T1 to T4 output the amplified signal (RF_{OUT}) of the RF signal (RF_{IN}) from their collectors via the capacitor C5.

A bias current I_{BIAS1} is supplied to one end of the resistor R11 and the other end of the resistor R11 is connected to the base of the transistor T1. The bias current I_{BIAS1} is supplied to one end of the resistor R12 and the other end of the resistor R12 is connected to the base of the transistor T2. The bias current I_{BIAS1} is supplied to one end of the resistor R13 and the other end of the resistor R13 is connected to the base of the transistor T3. The bias current I_{BIAS1} is supplied to one end of the resistor R14 and the other end of the resistor R14 is connected to the base of the transistor T4. A bias current I_{BIAS2} is supplied to one end of the resistor R23 and the other end of the resistor R23 is connected to the base of the transistor T3. The bias current I_{BIAS2} is supplied to one end of the resistor R24 and the other end of the resistor R24 is connected to the base of the transistor T4.

The bias circuit 200 generates the bias current I_{BIAS1} on the basis of a bias control voltage V_{BIAS1} . The bias circuit 200 includes a transistor T31, for example. The transistor T31 is an HBT, for example. The bias control voltage V_{BIAS1} is supplied to the base of the transistor T31, the power supply voltage V_{CC} is supplied to the collector of the transistor T31 and the emitter of the transistor T31 is connected to one end of each of the resistors R11 to R14.

The bias circuit 210 generates the bias current I_{BIAS2} on the basis of a bias control voltage V_{BIAS2} . The bias circuit 210 includes a transistor T32, for example. The transistor T32 is an HBT, for example. The bias control voltage V_{BIAS2} is supplied to the base of the transistor T32, the power supply voltage V_{CC} is supplied to the collector of the transistor T32 and the emitter of the transistor T32 is connected to one end of each of the resistors R23 and R24.

The bias control circuit 220 controls the bias control voltages V_{BIAS1} and V_{BIAS2} on the basis of the gain mode control voltage V_{MODE} . Specifically, at the time of the high gain mode, the bias control circuit 220 makes the bias control voltage V_{BIAS1} be at a high level and the bias control voltage V_{BIAS2} be at a low level. In addition, at the time of the low gain mode, the bias control circuit 220 makes the bias control voltage V_{BIAS2} be at the high level and the bias control voltage V_{BIAS1} be at the low level. The high level is a voltage that is higher than a threshold voltage at which the transistors T31 and T32 that form the bias circuits 200 and 210 switch on and the low level is a voltage that is lower than this threshold voltage.

Referring to FIGS. 3 and 4, an example of the operation of the power amplification module 120 will be described.

FIG. 3 is a diagram for explaining the operation of the power amplification module 120 in the case of the high gain mode. In the case of the high gain mode, the bias control circuit 220 makes the bias control voltage V_{BIAS1} be at the high level and the bias control voltage V_{BIAS2} be at the low level. Thus, the transistor T31 of the bias circuit 200 is switched on and the transistor T32 of the bias circuit 210 is switched off. The bias current I_{BIAS1} is outputted from the bias circuit 200.

The bias current I_{BIAS1} is supplied to the base of the transistor T1 via the resistor R11. Similarly, the bias current

I_{BIAS1} is supplied to the bases of the transistors T2 to T4 via the resistors R12 to R14, respectively. Thus, the transistors T1 to T4 are switched on and the RF signal (RF_{IN}) is amplified by the transistors T1 to T4.

FIG. 4 is a diagram for explaining the operation of the power amplification module 120 in the case of the low gain mode. In the case of the low gain mode, the bias control circuit 220 makes the bias control voltage V_{BIAS1} be at the low level and the bias control voltage V_{BIAS2} be at the high level. Thus, the transistor T31 of the bias circuit 200 is switched off and the transistor T32 of the bias circuit 210 is switched on. The bias current I_{BIAS2} is outputted from the bias circuit 210.

The bias current I_{BIAS2} is supplied to the base of the transistor T3 via the resistor R23. Similarly, the bias current I_{BIAS2} is supplied to the base of the transistor T4 via the resistor R24. Thus, the transistors T3 and T4 are switched on.

The bias current I_{BIAS2} is supplied to the base of the transistor T1 via the resistors R23, R13 and R11. Similarly, the bias current I_{BIAS2} is supplied to the base of the transistor T2 via the resistors R23, R13 and R12. In addition, the bias current I_{BIAS2} is supplied to the base of the transistor T1 via the resistors R24, R14 and R11. In addition, the bias current I_{BIAS2} is supplied to the base of the transistor T2 via the resistors R24, R14 and R12. However, the amount of the current supplied to the bases of the transistors T1 and T2 is small compared with the amount of the current supplied to the transistors T3 and T4. Consequently, although the transistors T1 and T2 are not entirely switched off, the size of the emitter current per unit emitter area is small compared with that for the transistors T3 and T4. Therefore, the gain generated by the transistors T1 to T4 is smaller than that in the case of the high gain mode illustrated in FIG. 3.

As described with reference to FIGS. 3 and 4, in the power amplification module 120, the transistors T1 to T4 are switched on by the bias current I_{BIAS1} being supplied to the bases of the transistors T1 to T4 in the case of the high gain mode. In addition, in the case of the low gain mode, the bias current I_{BIAS2} is supplied to the bases of the transistors T3 and T4 and the transistors T3 and T4 are switched on. Furthermore, the bias current I_{BIAS2} is also supplied to the bases of the transistors T1 and T2 via the resistors R13 and R14 and the transistors T1 and T2 enter a state of not being completely switched off.

In the power amplification module 120, the gain can be made to change through this type of operation. In the power amplification module 120, since the transistors T1 and T2 are not completely switched off in the case of the low gain mode, the change in the input impedance can be suppressed compared with the case where the transistors T1 and T2 are completely switched off.

In the power amplification module 120, the number of transistors that form the amplification circuit is four, but the number is not limited to this. Furthermore, in the power amplification module 120, the number of transistors for which the size of the supplied bias current becomes small at the time of the low gain mode is two (transistors T1 and T2), but the number is not limited to this. For example, the number of transistors for which the size of the supplied bias current becomes small at the time of the low gain mode may be three (for example, transistors T1 to T3) or one (for example, transistor T1).

Referring to FIGS. 5 and 6, the characteristics of the power amplification module 120 will be described.

FIG. 5 illustrates an example of the relationship between the number of transistors and the change in gain. The

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horizontal axis represents the number of transistors that are completely switched on and the vertical axis represents the change in gain, with a state in which the number of transistors that are directly contributing to amplification (that are completely switched on) is four serving as a reference.

In FIG. 5, the solid line represents an example of the simulation results for the same configuration as that of the power amplification module 120 of this embodiment (configuration in which a current is also supplied to transistors that do not directly contribute to amplification). In addition, the broken line represents an example of the simulation results for a typical configuration in which a current is not supplied to transistors that do not directly contribute to amplification. As illustrated in FIG. 5, in the same configuration as that of the power amplification module 120, the gain can be reduced by decreasing the number of transistors that directly contribute to amplification (are completely switched on) at the time of the low gain mode.

FIG. 6 illustrates an example of the relationship between the number of transistors and the voltage standing wave ratio. The horizontal axis represents the number of transistors that are completely switched on and the vertical axis represents the voltage standing wave ratio at the input of the power amplification module (input VSWR).

In FIG. 6, the solid line represents an example of the simulation results for the same configuration as that of the power amplification module 120 (configuration in which a current is also supplied to transistors that do not directly contribute to amplification). In addition, the broken line represents an example of the simulation results for a typical configuration in which a current is not supplied to transistors that do not directly contribute to amplification. As illustrated in FIG. 6, in the same configuration as that of the power amplification module 120, since there are transistors that are not completely switched off at the time of the low gain mode, the change in input impedance is suppressed and as a result the degradation of the input VSWR can be suppressed.

An exemplary embodiment of the present disclosure has been described above. According to the power amplification module 120, the transistors T1 and T2 are not completely switched off at the time of the low gain mode. Consequently, a change in the input impedance that occurs with a change in the gain can be suppressed in the power amplification module 120.

Although the power amplification module 120 is a single-stage amplification circuit, the present disclosure can be similarly applied to an amplification circuit having two or more stages. In the case where the present disclosure is applied to an amplification circuit having two or more stages, the same configuration may be adopted in all of the stages or the same configuration may be adopted in only some of the stages.

The purpose of the embodiment described above is to enable easy understanding of the present disclosure and the embodiment is not to be interpreted as limiting the present disclosure. The present disclosure can be modified or improved without departing from the gist of the disclosure and equivalents to the present disclosure are also included in the present invention. In other words, appropriate design modifications made to the embodiments by one skilled in the art are included in the scope of the present disclosure so long as the modifications have the characteristics of the present disclosure. For example, the elements included in the embodiments and the arrangements, materials, conditions, shapes, sizes and so forth of the elements are not limited to those exemplified in the embodiments and can be appropri-

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ately changed. In addition, the elements included in the embodiments can be combined as much as technically possible and such combined elements are also included in the scope of the present disclosure so long as the combined elements have the characteristics of the present disclosure.

While preferred embodiments of the disclosure have been described above, it is to be understood that variations and modifications will be apparent to those skilled in the art without departing from the scope and spirit of the disclosure. The scope of the disclosure, therefore, is to be determined solely by the following claims.

What is claimed is:

1. A power amplification module comprising:

a first transistor, a first signal being inputted to a base of the first transistor;

a second transistor, the first signal being inputted to a base of the second transistor and a collector of the second transistor being connected to a collector of the first transistor;

a first resistor, a first bias current being supplied to one end of the first resistor and another end of the first resistor being connected to the base of the first transistor;

a second resistor, one end of the second resistor being connected to the one end of the first resistor and another end of the second resistor being connected to the base of the second transistor; and

a third resistor, a second bias current being supplied to one end of the third resistor and another end of the third resistor being connected to the base of the second transistor;

wherein, at the time of a high gain mode, the first bias current is supplied to the bases of the first and second transistors via the first and second resistors, respectively,

at the time of a low gain mode, the second bias current is supplied to the base of the second transistor via the third resistor and is supplied to the base of the first transistor via the third, second and first resistors, and a second signal obtained by amplifying the first signal is outputted from the collectors of the first and second transistors.

2. The power amplification module according to claim 1, further comprising:

a third transistor, a first bias control voltage being supplied to a base of the third transistor and the first bias current being outputted from an emitter of the third transistor; and

a fourth transistor, a second bias control voltage being supplied to a base of the fourth transistor and the second bias current being outputted from an emitter of the fourth transistor;

wherein the one end of the first resistor and the one end of the second resistor are connected to the emitter of the third transistor, and the one end of the third resistor is connected to the emitter of the fourth transistor.

3. The power amplification module according to claim 2, further comprising:

a bias control circuit, at the time of the high gain mode, making the first bias control voltage be at a level of switching on the third transistor and making the second bias control voltage be at a level of switching off the fourth transistor, and

at the time of the low gain mode, making the first bias control voltage be at a level of switching off the third

transistor and making the second bias control voltage be at a level of switching on the fourth transistor.

4. The power amplification module according to claim 1, wherein the power amplification module is adapted to suppress a change in input impedance that occurs with a change in gain. 5

5. The power amplification module according to claim 2, wherein the power amplification module is adapted to suppress a change in input impedance that occurs with a change in gain. 10

6. The power amplification module according to claim 3, wherein the power amplification module is adapted to suppress a change in input impedance that occurs with a change in gain. 15

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